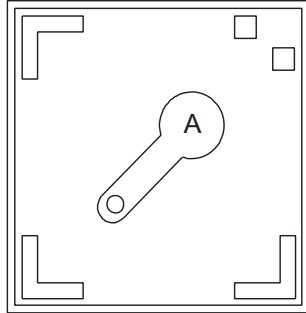


CPD65-BAV45

Low Leakage Diode Die

50mA, 35 Volt

The CPD65-BAV45 is a silicon 50mA, 35 Volt diode ideal for low leakage applications.



BACKSIDE CATHODE R0

MECHANICAL SPECIFICATIONS:

| | |
|------------------------|--------------------|
| Die Size | 11.8 x 11.8 MILS |
| Die Thickness | 8.0 MILS |
| Anode Bonding Pad Size | 2.35 MILS DIAMETER |
| Top Side Metalization | Al – 15,000Å |
| Back Side Metalization | Au – 18,000Å |
| Scribe Alley Width | 2.5 MILS |
| Wafer Diameter | 4 INCHES |
| Gross Die Per Wafer | 75,000 |

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

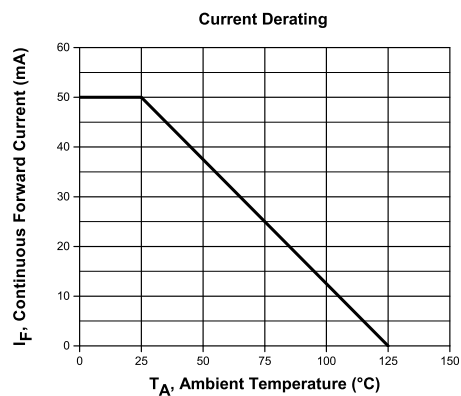
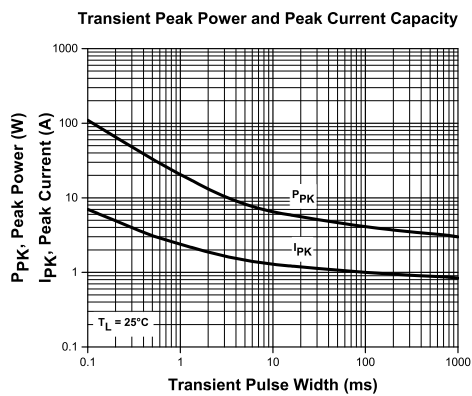
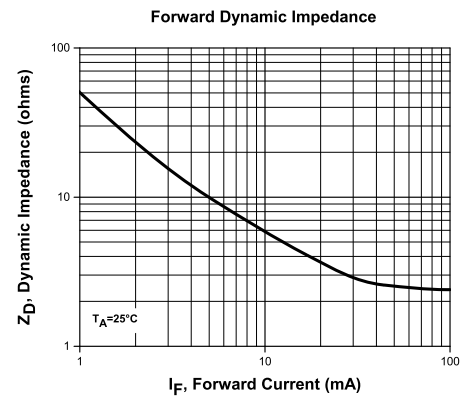
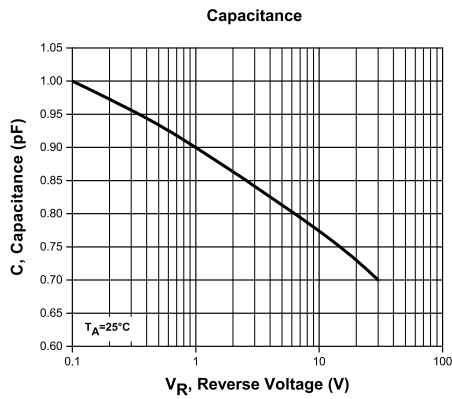
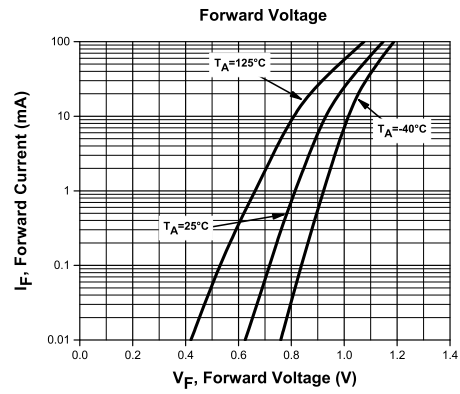
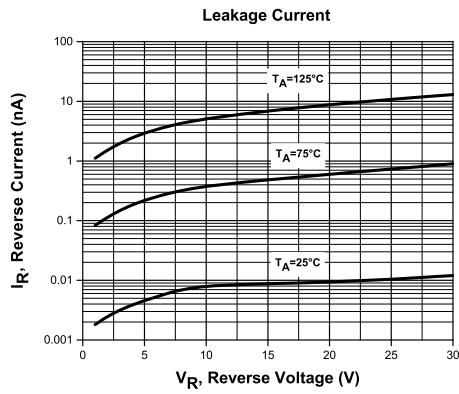
| | SYMBOL | | UNITS |
|--|----------------|-------------|------------------|
| Peak Repetitive Reverse Voltage | V_{RRM} | 35 | V |
| Continuous Reverse Voltage | V_R | 20 | V |
| Continuous Forward Current | I_F | 50 | mA |
| Peak Repetitive Forward Current | I_{FRM} | 100 | mA |
| Operating and Storage Junction Temperature | T_J, T_{stg} | -65 to +125 | $^\circ\text{C}$ |

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

| SYMBOL | TEST CONDITIONS | MIN | MAX | UNITS |
|----------|---|-----|-----|-------|
| I_R | $V_R=5.0\text{V}$ | | 5.0 | pA |
| I_R | $V_R=20\text{V}$ | | 10 | pA |
| V_F | $I_F=10\text{mA}$ | | 1.0 | V |
| C_J | $V_R=0, f=1.0\text{MHz}$ | | 1.3 | pF |
| t_{rr} | $I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$ | | 600 | ns |

CPD65-BAV45

Typical Electrical Characteristics



BARE DIE PACKING OPTIONS



BARE DIE IN TRAY (WAFFLE) PACK

CT: Singulated die in tray (waffle) pack.
(example: CP211-PART NUMBER-CT)

CM: Singulated die in tray (waffle) pack 100% visually inspected as per MIL-STD-750, (method 2072 transistors, method 2073 diodes).
(example: CP211-PART NUMBER-CM)



UNSAWN WAFER

WN: Full wafer, unsawn, 100% tested with reject die inked.
(example: CP211-PART NUMBER-WN)



SAWN WAFER ON PLASTIC RING

WR: Full wafer, sawn and mounted on plastic ring,
100% tested with reject die inked.
(example: CP211-PART NUMBER-WR)

Please note: Sawn Wafer on Metal Frame (WS) is possible as a special order. Please contact your Central Sales Representative at 631-435-1110.



Visit the Central website for a complete listing of specifications:
www.centrasemi.com/bdspecs

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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